# PEMD2; PIMD2; PUMD2

# NPN/PNP resistor-equipped transistors; $R1 = 22 k\Omega$ , $R2 = 22 k\Omega$

Rev. 8 — 14 November 2013

**Product data sheet** 

# **Product profile**

#### 1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview** 

.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			NPN/NPN	Package	
	NXP	JEITA	complement	complement	configuration
PEMD2	SOT666	-	PEMB1	PEMH1	ultra small and flat lead
PIMD2	SOT457	SC-74	-	-	small
PUMD2	SOT363	SC-88	PUMB1	PUMH1	very small

#### 1.2 Features and benefits

- 100 mA output current capability Reduces component count
- Built-in bias resistors
- Simplifies circuit design
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor; for the PNP transistor	with negative po	olarity			
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



# 2. Pinning information

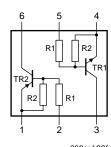
Table 3. Pinning

Table 5.	i iiiiiiig				
Pin	Description	Simplified outline	Graphic symbol		
PEMD2 (	SOT666); PUMD2 (SOT363)				
1	GND (emitter) TR1				
2	input (base) TR1	6   5   4	6 5 4		
3	output (collector) TR2				
4	GND (emitter) TR2		R1 R2		
5	input (base) TR2		TR1		
6	output (collector) TR1	001aab555	R2 R1		
			1 2 3		
			006aaa143		

#### **PIMD2 (SOT457)**

	•	
1		GND (emitter) TR2
2		input (base) TR2
3		output (collector) TR1
4		GND (emitter) TR1
5		input (base) TR1
6		output (collector) TR2





006aab235

# 3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PEMD2	-	plastic surface-mounted package; 6 leads	SOT666			
PIMD2	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457			
PUMD2	SC-88	plastic surface-mounted package; 6 leads	SOT363			

# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD2	D4
PIMD2	M5
PUMD2	D*2

[1] \* = placeholder for manufacturing site code

PEMD2\_PIMD2\_PUMD2

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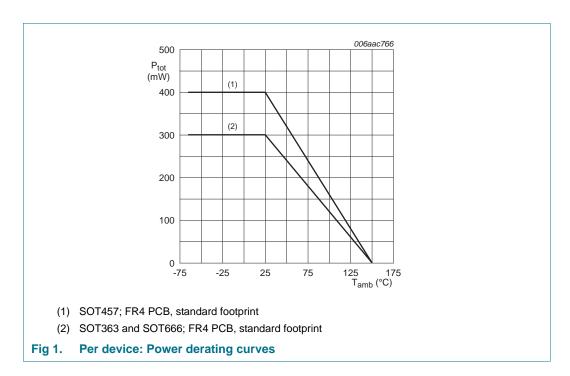
# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transi	stor; for the PNP transistor	with negative polari	ity		
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V
VI	input voltage TR1				
	positive		-	+40	V
	negative		-	-10	V
	input voltage TR2				
	positive			+10	
	negative			-40	
lo	output current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMD2 (SOT666)		[1] -	200	mW
	PIMD2 (SOT457)		[1]	250	mW
	PUMD2 (SOT363)		[1] -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMD2 (SOT666)		[1] -	300	mW
	PIMD2 (SOT457)		[1]	400	mW
	PUMD2 (SOT363)		[1] -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



# 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMD2 (SOT666)		<u>[1]</u> -	-	625	K/W
	PIMD2 (SOT457)		<u>[1]</u> -	-	500	K/W
	PUMD2 (SOT363)		<u>[1]</u> -	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMD2 (SOT666)		[1] -	-	417	K/W
	PIMD2 (SOT457)		[1] -	-	313	K/W
	PUMD2 (SOT363)		[1] -	-	417	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

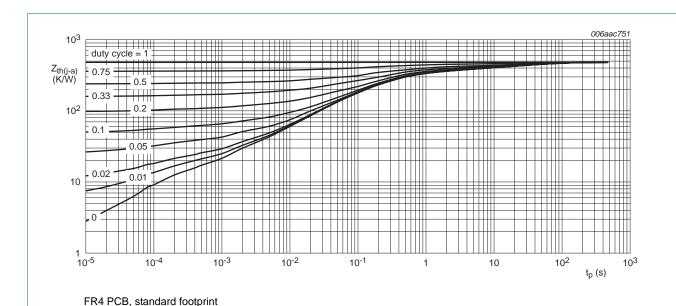


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMD2 (SOT666); typical values

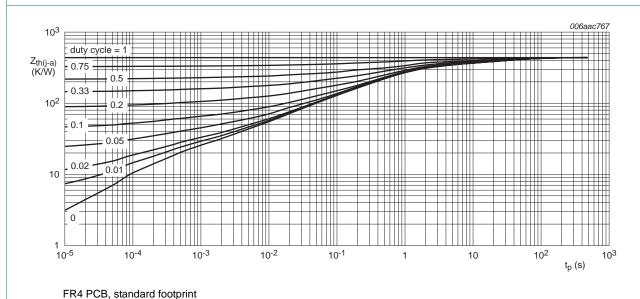


Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PIMD2 (SOT457); typical values

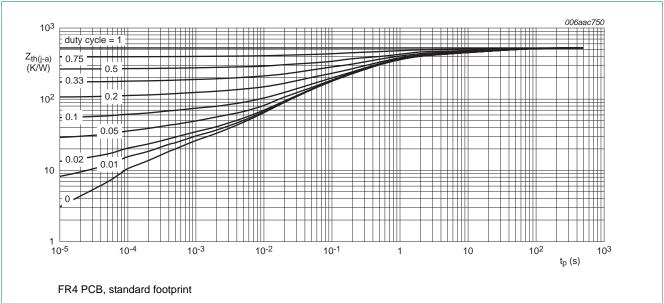


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMD2 (SOT363); typical values

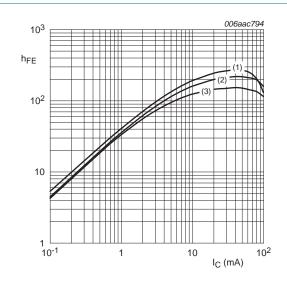
# 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor; for the PNP trans	sistor with negative polarity				
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	100	nΑ
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	8.0	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	2.5	1.7	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	$k\Omega$
R2/R1	bias resistor ratio		8.0	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz				
	TR1 (NPN)		-	230	-	MHz
	TR2 (PNP)		-	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor



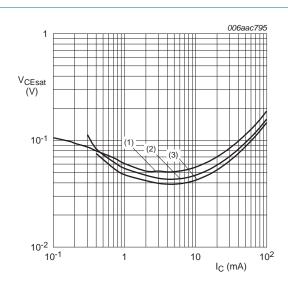
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 5. TR1 (NPN): DC current gain as a function of collector current; typical values



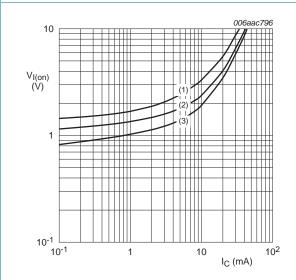
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



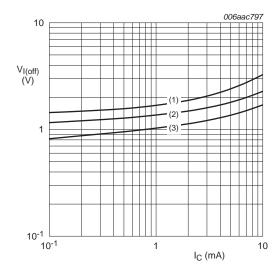
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 7. TR1 (NPN): On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. TR1 (NPN): Off-state input voltage as a function of collector current; typical values

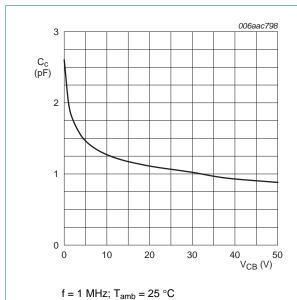
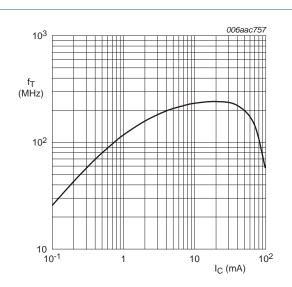
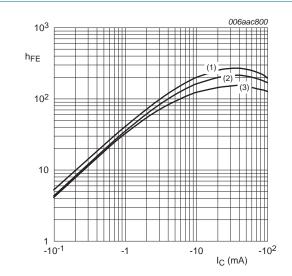


Fig 9. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



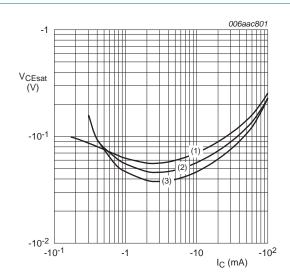
 $V_{CE} = 5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig 10. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



- $V_{CE} = -5 \text{ V}$
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

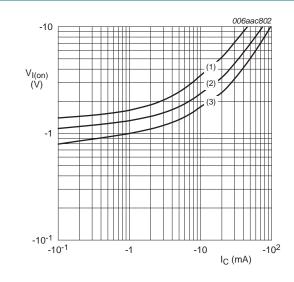
Fig 11. TR2 (PNP): DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

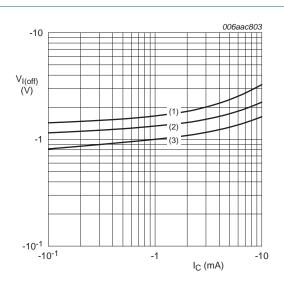
Fig 12. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = -0.3 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 13. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 14. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

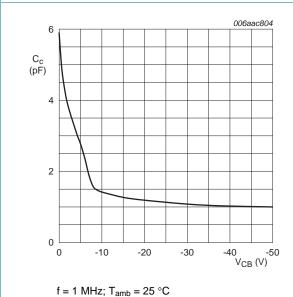
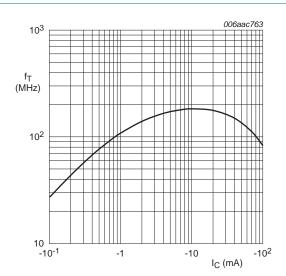


Fig 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

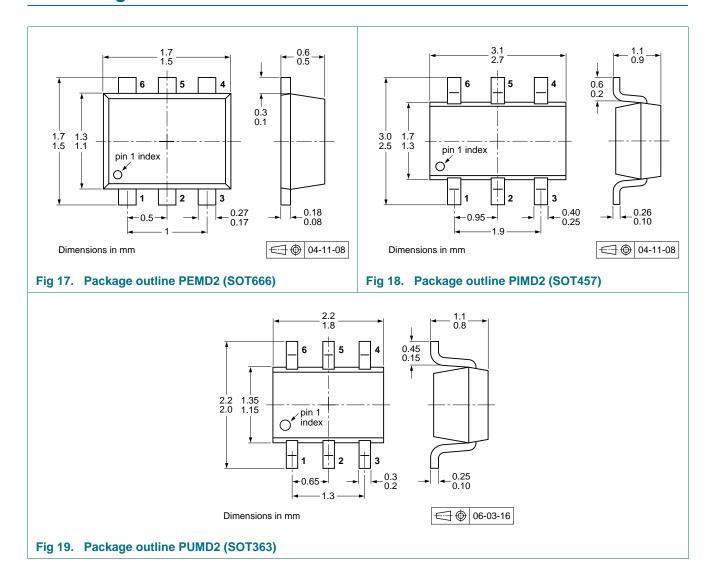
Fig 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

## 8. Test information

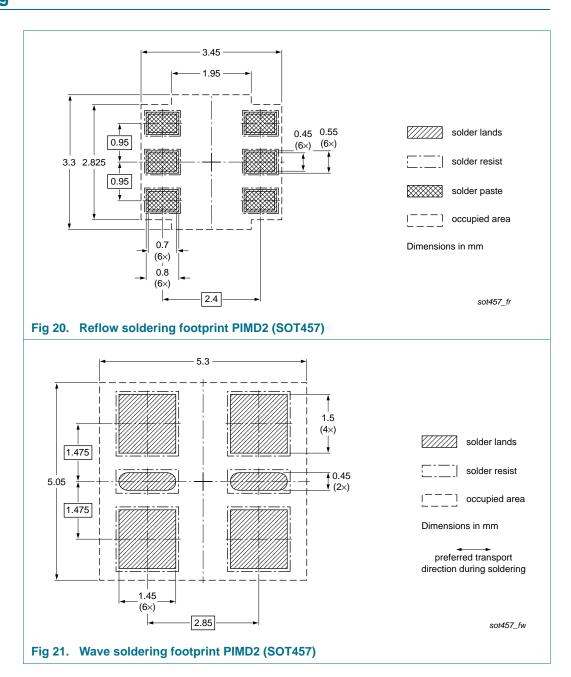
#### 8.1 Quality information

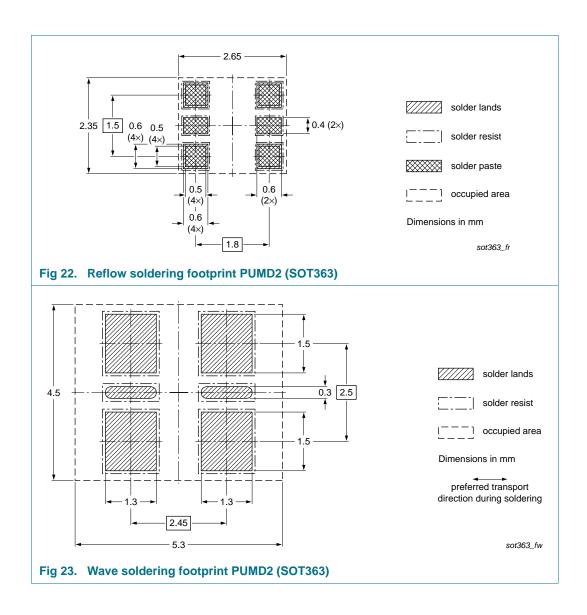
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

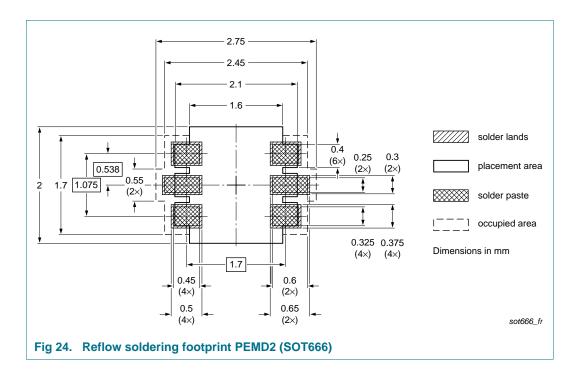
# 9. Package outline



# 10. Soldering







# 11. Revision history

#### Table 9. Revision history

Release date	Data sheet status	Change notice	Supersedes
20131114	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.7
Section 1 '	'Product profile": updated	I	
<ul> <li>Section 4 '</li> </ul>	'Marking": updated		
• Figure 1 to	o <u>4, 9</u> , <u>10, 15</u> and <u>16</u> : add	ed	
<ul> <li>Section 5 '</li> </ul>	'Limiting values": updated	t	
<ul> <li>Section 6 '</li> </ul>	'Thermal characteristics":	updated	
• Figure 5 to	8 and 11 to 14: updated		
<ul> <li>Table 8 "C</li> </ul>	haracteristics": I <sub>CEO</sub> upda	ited, f <sub>T</sub> added	
<ul> <li>Section 8 '</li> </ul>	'Test information": added		
<ul> <li>Section 12</li> </ul>	"Legal information": upd	ated	
20080924	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.6
20042104	Product specification	-	PEMD2_PIMD2_PUMD2 v.5
20030606	Product specification	-	-
	20131114	Section 1 "Product profile": updated     Section 4 "Marking": updated     Figure 1 to 4, 9, 10, 15 and 16: add     Section 5 "Limiting values": updated     Section 6 "Thermal characteristics":     Figure 5 to 8 and 11 to 14: updated     Table 8 "Characteristics": I <sub>CEO</sub> updated     Section 8 "Test information": added     Section 12 "Legal information": upd	Section 1 "Product profile": updated  Section 4 "Marking": updated  Figure 1 to 4, 9, 10, 15 and 16: added  Section 5 "Limiting values": updated  Section 6 "Thermal characteristics": updated  Figure 5 to 8 and 11 to 14: updated  Table 8 "Characteristics": I <sub>CEO</sub> updated, f <sub>T</sub> added  Section 8 "Test information": added  Section 12 "Legal information": updated  20080924 Product data sheet  Product specification  Product specification

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMD2\_PIMD2\_PUMD2

# PEMD2; PIMD2; PUMD2

#### NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

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# PEMD2; PIMD2; PUMD2

NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

## 14. Contents

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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